

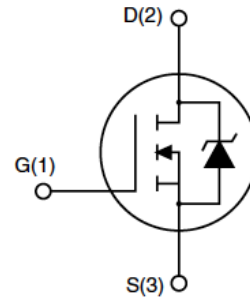
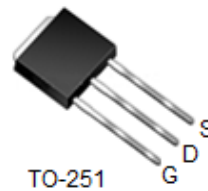
Features

V_{DSS}	$R_{DS(ON)}$ @ 10V (typ)	I_D
200V	0.21 Ω	9A

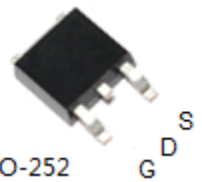
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

Application

- DC Motor Control and Class D Amplifier
- Uninterruptible Power Supply (UPS)
- Automotive

**Schematic diagram**

TO-251



TO-252

Ordering Information

Part Number	Marking	Case	Packaging
630A	630A	TO-251	72pcs/Tube
630A	630A	TO-252	2500pcs/Reel

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter		Max.	Units
			TO-251/TO-252	
V_{DSS}	Drain-Source Voltage		200	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	9	A
		$T_C = 100^\circ\text{C}$	5.83	A
I_{DM}	Pulsed Drain Current ^{note1}		36	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		320	mJ
dv/dt	Peak Diode Recovery Energy ^{note3}		5	V/ns
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	83	W
	Linear Derating Factor	$T_C > 25^\circ\text{C}$	0.67	W/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.5	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	200	-	-	V
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D = 250μA	-	0.25	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V	-	-	1	μA
		V _{DS} = 160V, T _C = 125°C	-	-	10	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage ^{note4}	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	3	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D = 4.5A	-	0.21	0.28	Ω
g _{FS}	Forward Transconductance	V _{DS} =30V, I _D = 4.5A	-	9.2	-	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	509	-	pF
C _{oss}	Output Capacitance		-	51.5	-	pF
C _{rss}	Reverse Transfer Capacitance		-	3.2	-	pF
Q _g	Total Gate Charge	V _{DD} = 160V, I _D = 9A, V _{GS} = 10V	-	11.8	-	nC
Q _{gs}	Gate-Source Charge		-	2.36	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.98	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100V, I _D = 9A, RG = 10Ω, VGS = 10V	-	10.33	-	ns
t _r	Turn-On Rise Time		-	10.7	-	ns
t _{d(off)}	Turn-Off Delay Time		-	29.1	-	ns
t _f	Turn-Off Fall Time		-	11.1	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	9	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	36	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 4.5A	-	-	14	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _F = 9A,	-	201	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt =100A/μs	-	663	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10mH, I_{AS} = 8A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. $I_{SD} \leq 9A, di/dt \leq 200A/\mu s, V_{DD} \leq B_{VDSS}$, Starting $T_J = 25^{\circ}\text{C}$
4. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

Typical Performance Characteristics

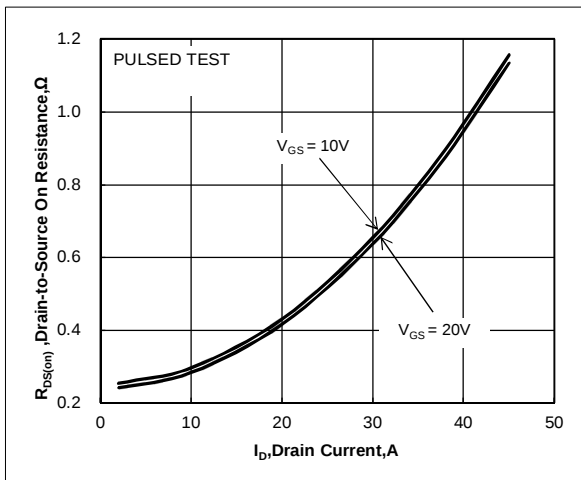


Figure 1. Drain-to-Source On Resistance vs. Drain Current and Gate Voltage

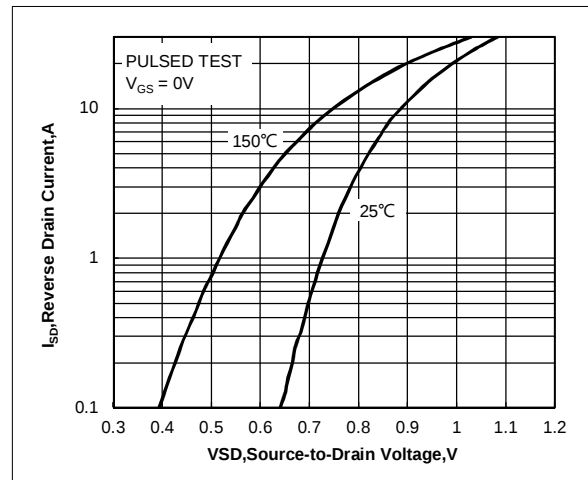


Figure 2. Body Diode Forward Voltage vs. Source Current and Temperature

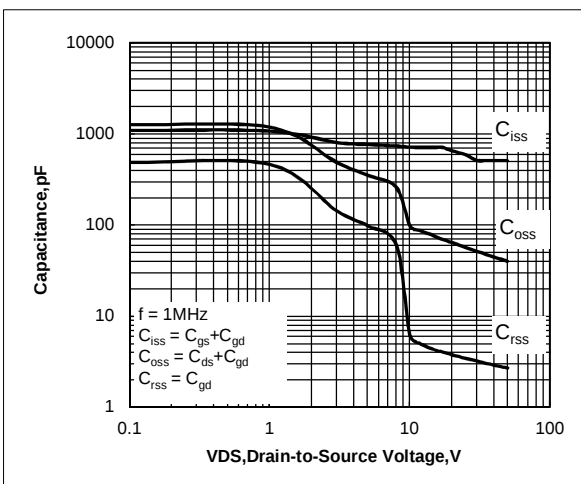


Figure 3. Capacitance Characteristics

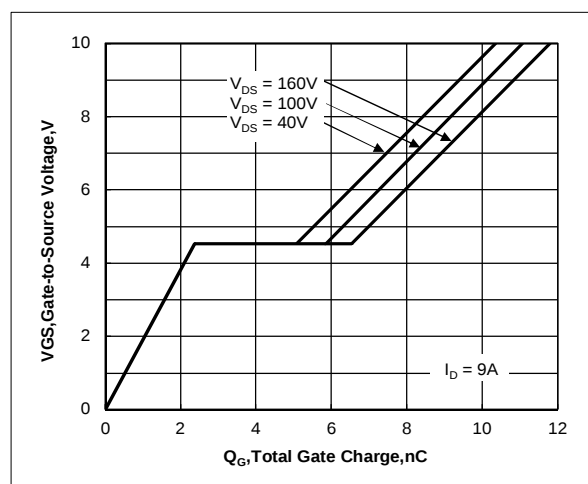


Figure 4. Gate Charge Characteristics

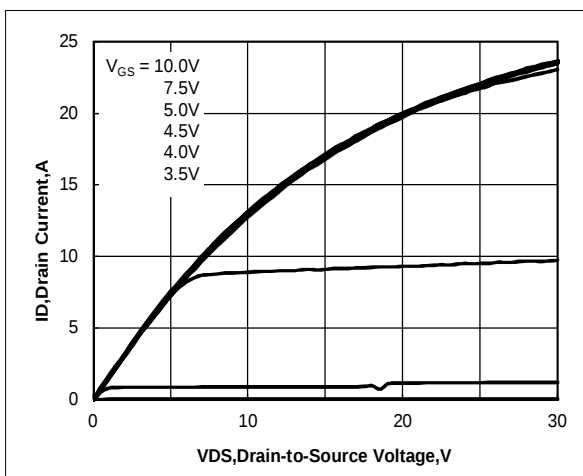


Figure 5. Output Characteristics

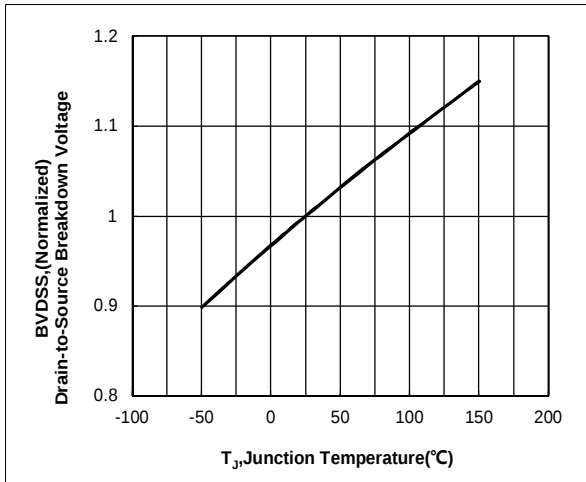


Figure 6. Normalized Breakdown Voltage vs. Junction Temperature

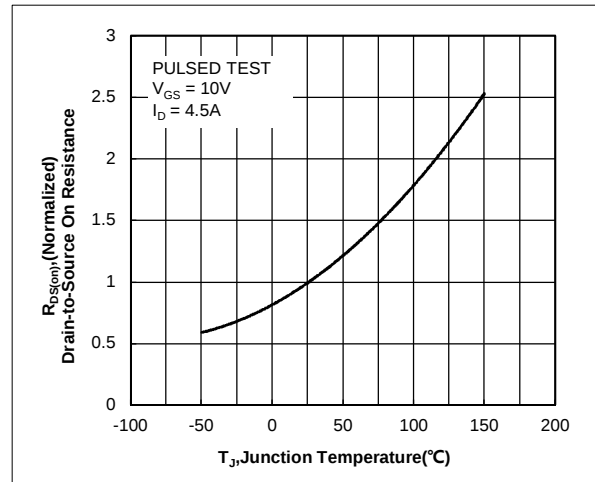


Figure 7. Normalized On Resistance vs. Junction Temperature

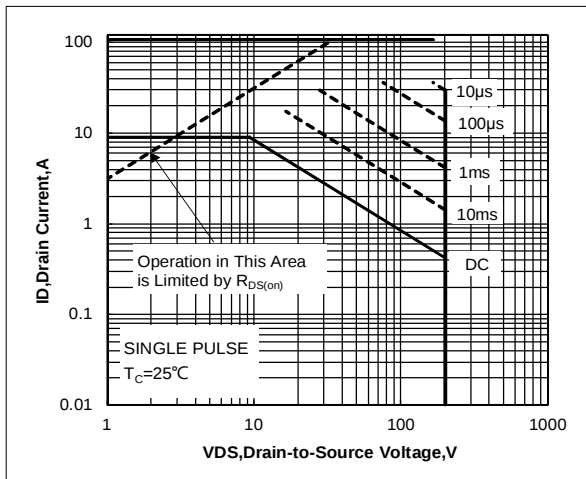


Figure 8. Maximum Safe Operating Area for RU920A

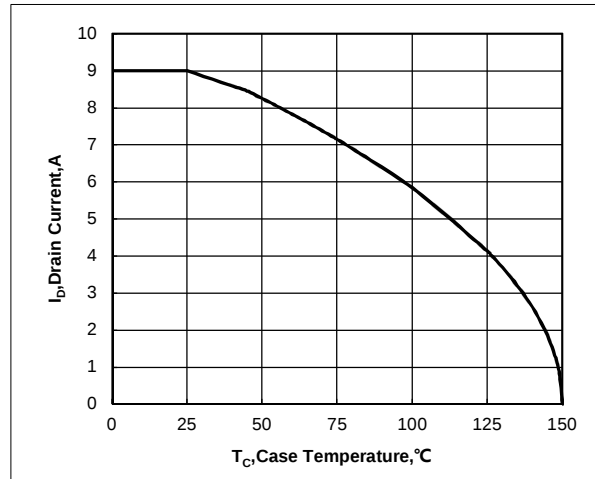


Figure 9. Maximum Continuous Drain Current vs. Case Temperature

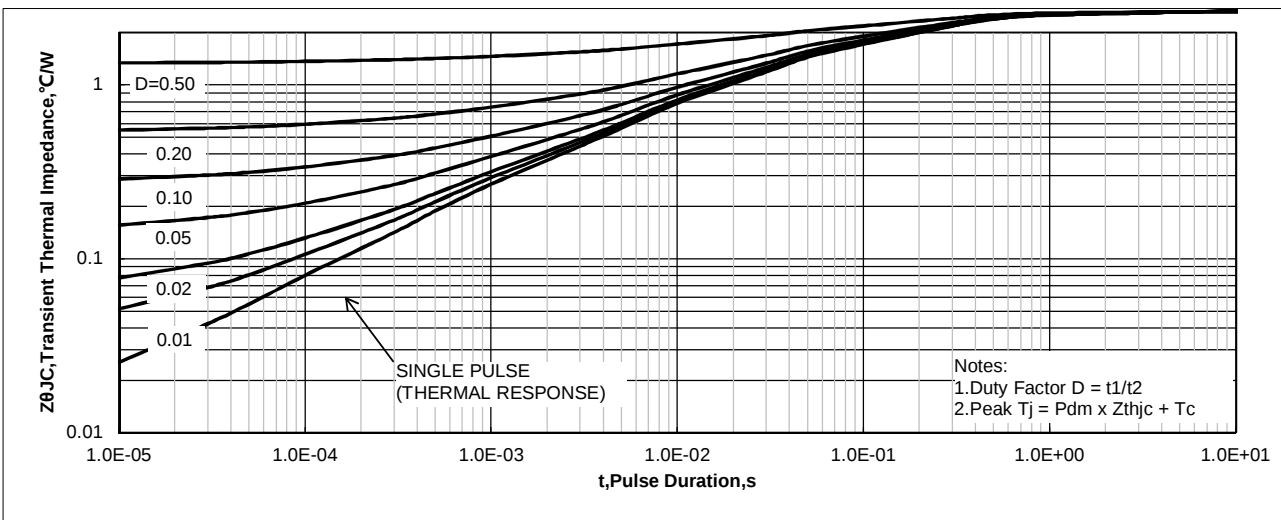


Figure 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case for RU920A

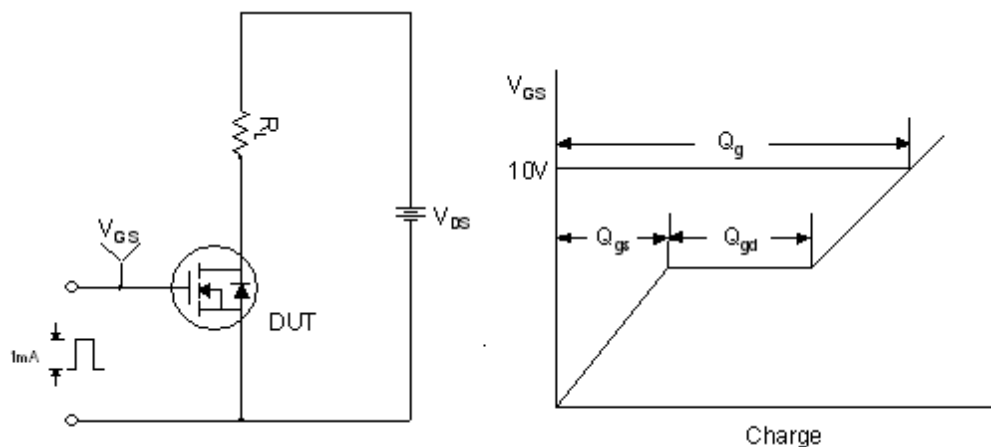


Figure 11. Gate Charge Test Circuit & Waveform

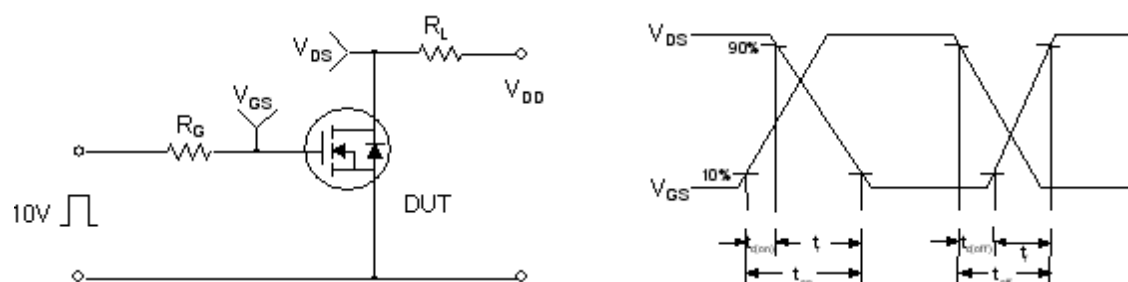


Figure 12. Resistive Switching Test Circuit & Waveforms

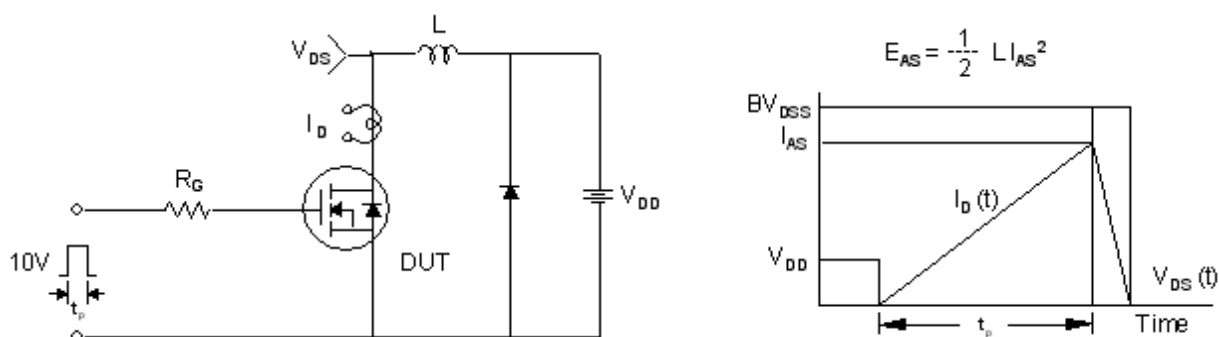
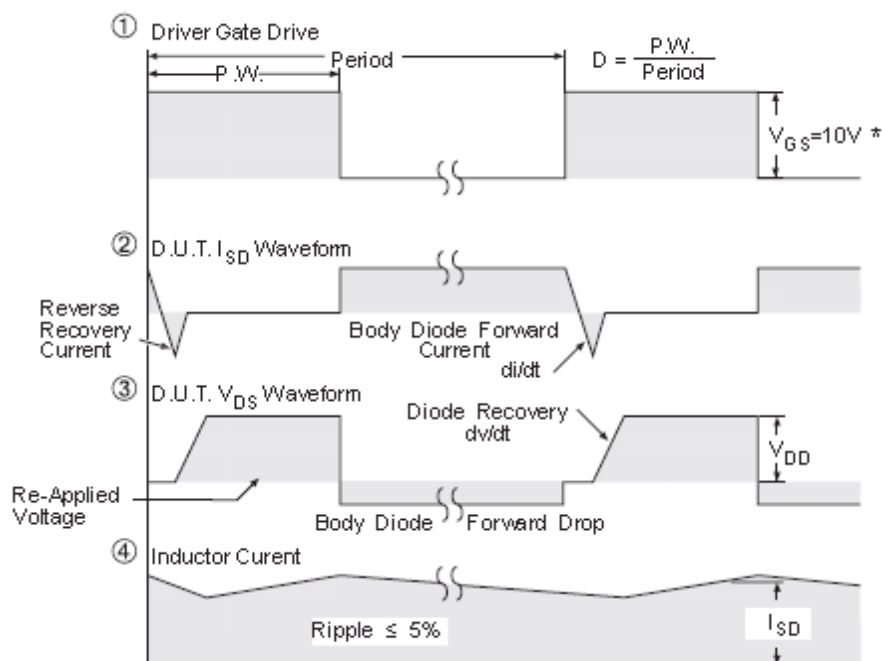
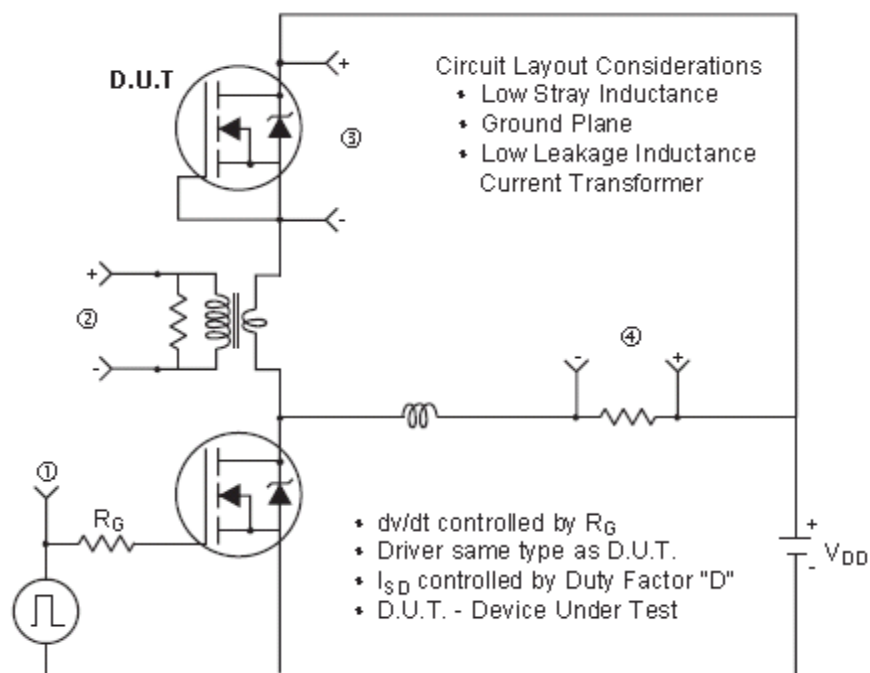


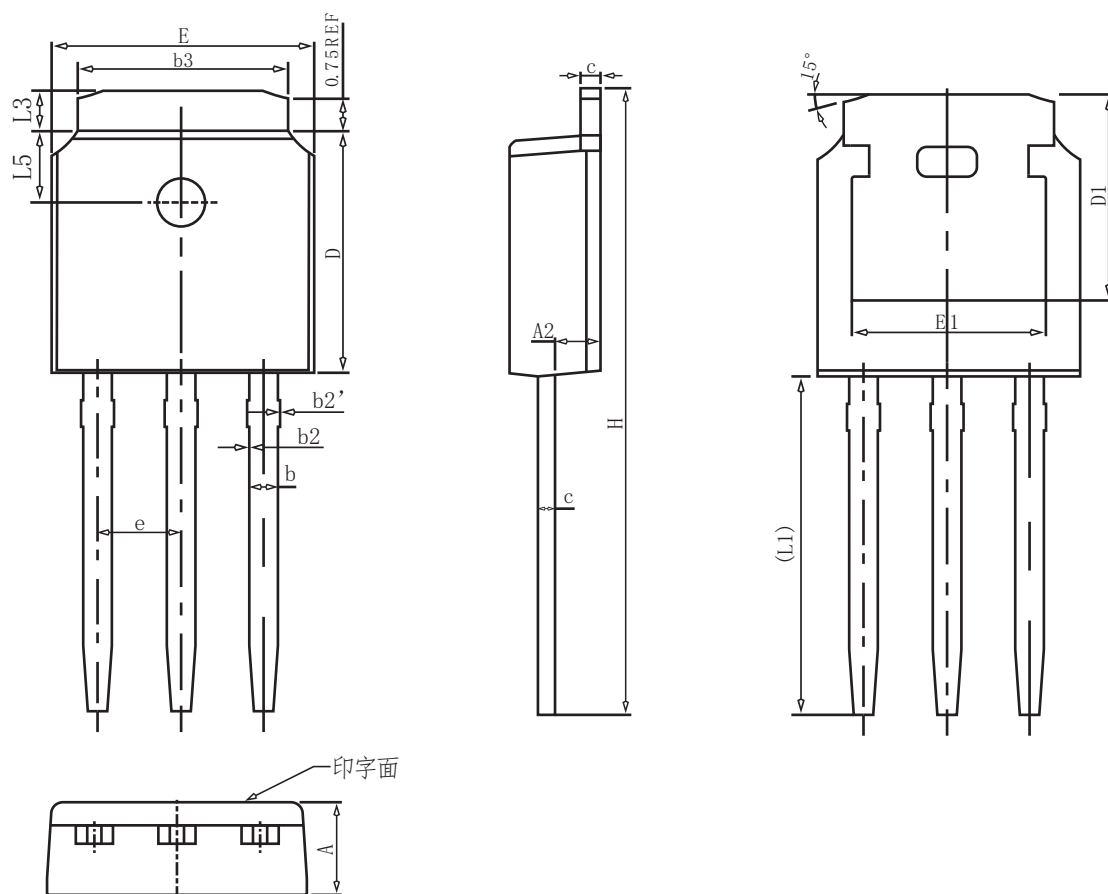
Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

Figure 14. Peak Diode Recovery and Switching Loss Test Circuit & Waveforms (For N-channel)

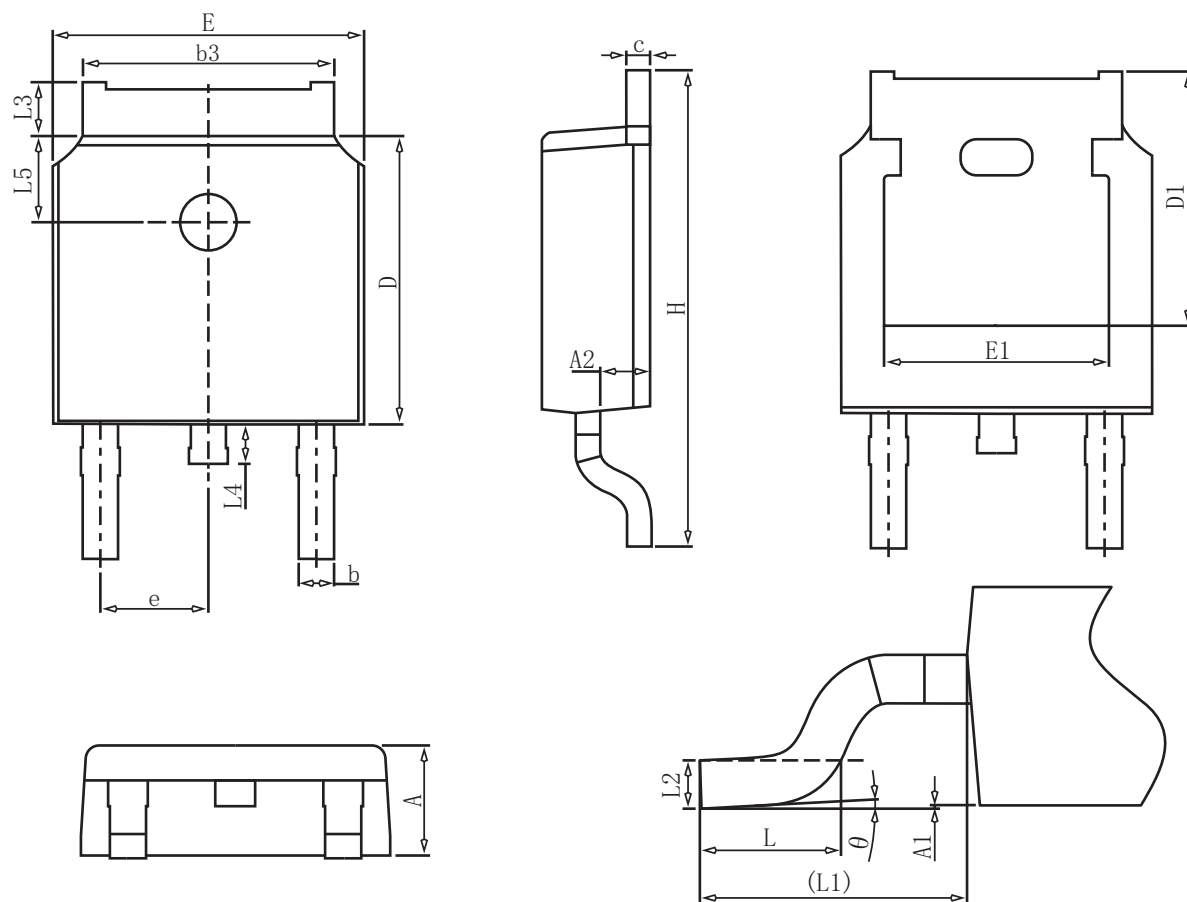
TO-251 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

TO-252 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	—	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	—	—
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	—	1.28
L4	0.50	—	1.00
L5	1.65	1.80	1.95
θ	0°	—	8°